Example Steps for Photolithography Processing

	For patterning electrodes with a sacrificial layer	For patterning negative master onto a silicon mold
Spin Coat	1. On a 75 x 50 mm glass slide, drop cast Microposit S1813 positive photoresist	1. On a 3” silicon wafer, drop cast SU-8 3025 negative photoresist
	2. Spin at 3000 rpm for 30 s to achieve a target thickness of 1.5 µm	2. Spin using the manufacturer’s spin curve to achieve the target thickness determined in step 1.4
Softbake	3. 100 °C for 1 min	3. 95 °C for 10 min
Expose	4. Align mask and slide with a UV mask aligner	4. Align mask and wafer with a UV mask aligner
	5. Expose the slide with a total radiant energy density of 300 mJ/cm^2	5. Expose the wafer with a total radiant energy density of 100–300 mJ/cm^2, depending on thickness
Post-Exposure Bake	n/a	6. 65 °C for 1 min
		7. 95 °C for 3 min
Develop	6. Immerse the slide in Microposit MF-321 developer for 20 s with gentle agitation.	8. Immerse wafer in SU-8 developer for 4 min, followed by 1 min of gentle agitation
Rinse	7. Rinse the slide with DI water	9. Rinse the slide with IPA and DI water
	8. Dry the slide with dry N_2.	10. Dry with dry N_2
Hard Bake	n/a	11. 150 °C for 5 min